Features

- Split Gate Trench MOSFET Technology
- Excellent Package for Heat Dissipation
- High Density Cell Design for Low $R_{DS(on)}$
- Halogen Free Available Upon Request By Adding Suffix "-HF"
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

N-CHANNEL MOSFET

Maximum Ratings

- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 40°C/W Junction to Ambient (1)
- Thermal Resistance: 0.25°C/W Junction to Case (1)

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Volltage		V_{GS}	±20	V
Continuous Drain Current	T_C=25°C	I_D	300	A
	T_C=100°C		267	A
Pulsed Drain Current (2)		I_{DM}	1200	A
Total Power Dissipation		P_D	500	W
Single Pulsed Avalanche Energy(3)		E_{AS}	800	mJ

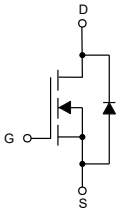
Note:

1.Surface Mounted on Minimum Footprint Pad Area.

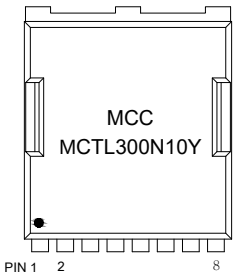
2.Pulse Test: Pulse Width≤10μs,Duty Cycle ≤1%.

3.T_J=25°C, L=1.0mH, V_{DD}=50V.

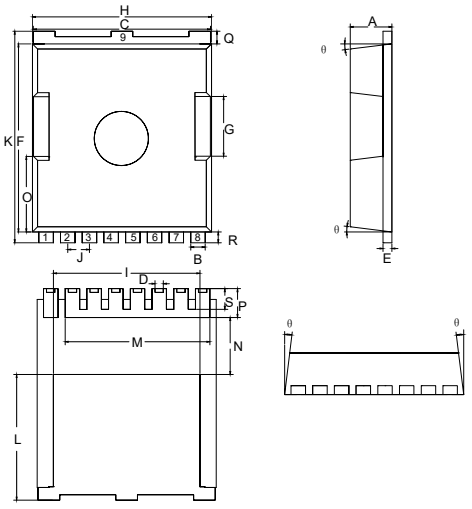
Internal Structure and Marking Code



1. GATE
2,3,4,5,6,7,8. SOURCE
9. DRAIN



TOLL-8L



DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.087	0.094	2.20	2.40	
B	0.028	0.035	0.70	0.90	
C	0.382	0.390	9.70	9.90	
D	0.017	0.020	0.42	0.50	
E	0.016	0.024	0.40	0.60	
F	0.405	0.417	10.28	10.58	
G	0.122	0.138	3.10	3.50	
H	0.382	0.398	9.70	10.10	
I	0.311	0.327	7.90	8.30	
J	0.047		1.20		BSC
K	0.452	0.468	11.48	11.88	
L	0.266	0.281	6.75	7.15	
M	0.315		8.00		
N	0.118	0.130	3.00	3.30	
O	0.157	0.172	3.98	4.38	
P	0.055	0.071	1.40	1.80	
Q	0.024	0.031	0.60	0.80	
R	0.020	0.028	0.50	0.70	
S	0.039	0.051	1.00	1.30	
θ	4°	10°	4°	10°	

Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=250μA	100			V
Gate-Source Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS} =±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=80V, V_{GS}=0V			1	μA
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250μA	2		4	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=30A		1.2	1.45	mΩ
		V_{GS}=6V, I_D=15A		1.48	1.9	mΩ
Diode Characteristics						
Continuous Body Diode Current	I_S				300	A
Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=30A			1.3	V
Reverse Recovery Time	t_{rr}	I_S=30A,di/dt=100A/μs		124		ns
Reverse Recovery Charge	Q_{rr}			388		nC
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS}=50V,V_{GS}=0V,f=1MHz		13258		pF
Output Capacitance	C_{oss}			2058		
Reverse Transfer Capacitance	C_{rss}			111		
Total Gate Charge	Q_g	V_{DS}=50V,V_{GS}=10V,I_D=30A		240		nC
Gate-Source Charge	Q_{gs}			60		
Gate-Drain Charge	Q_{gd}			59		
Turn-On Delay Time	$t_{d(on)}$	V_{DS}=50V, V_{GEN}=10V, R_G=4.5Ω, R_L=1.66Ω, I_{DS}=30A		33		ns
Turn-On Rise Time	t_r			69		
Turn-Off Delay Time	$t_{d(off)}$			172		
Turn-Off Fall Time	t_f			105		

Curve Characteristics

Fig. 1 - Typical Output Characteristics

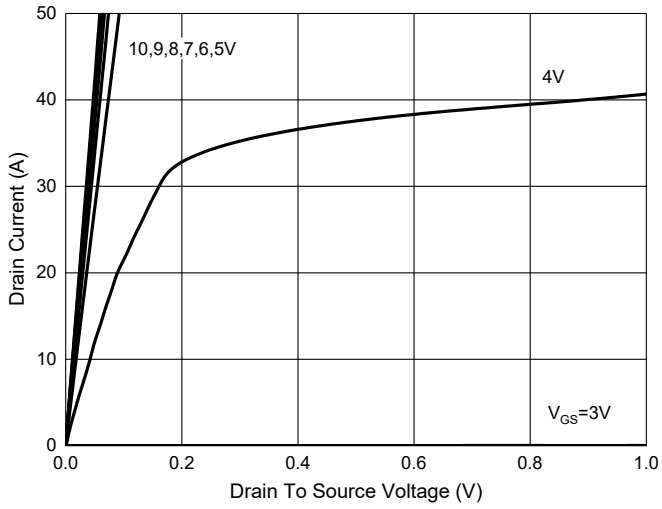


Fig. 2 - $R_{DS(ON)}$—V_{GS}

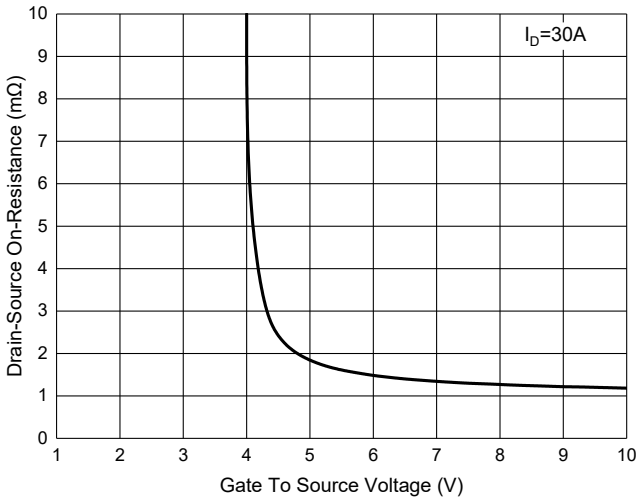


Fig. 3 - $R_{DS(ON)}$—I_D

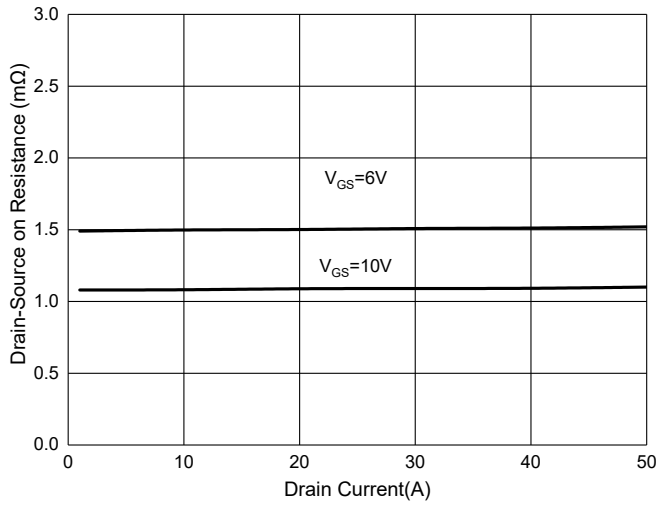


Fig. 4 - Normalized On Resistance Characteristics

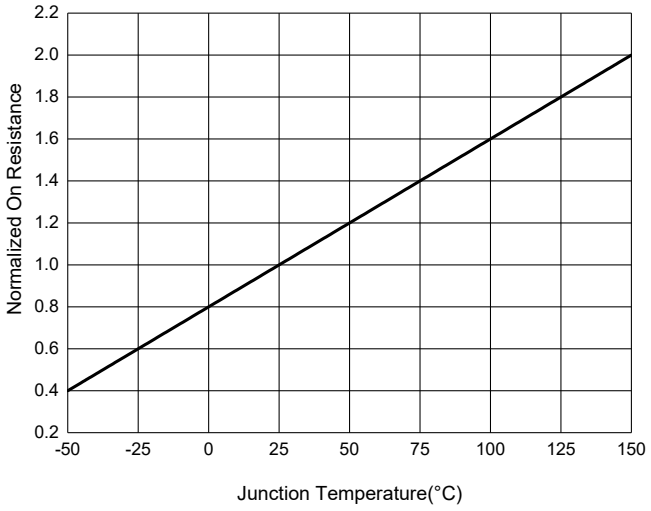


Fig. 5 - Capacitance Characteristics

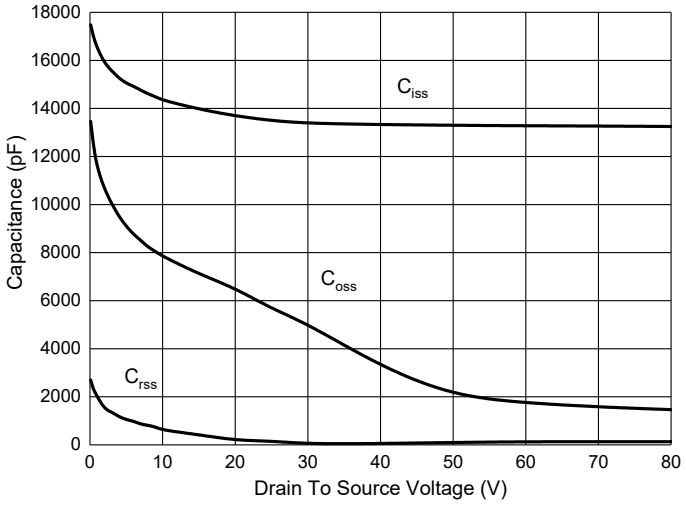
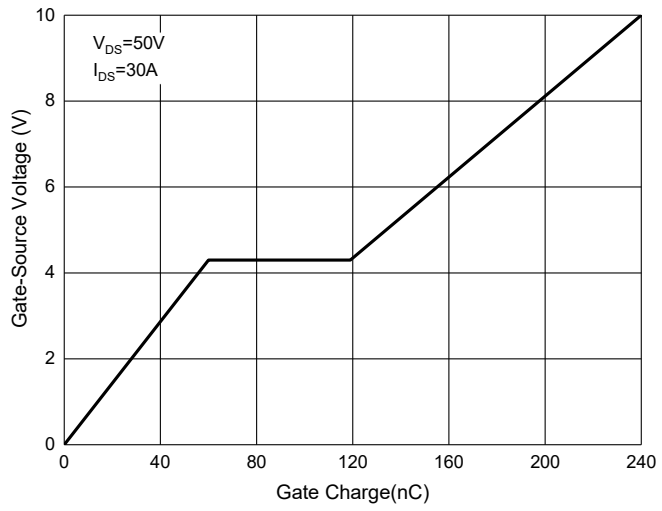


Fig. 6 - Gate Charge



Curve Characteristics

Fig. 7 - I_S—V_{SD}

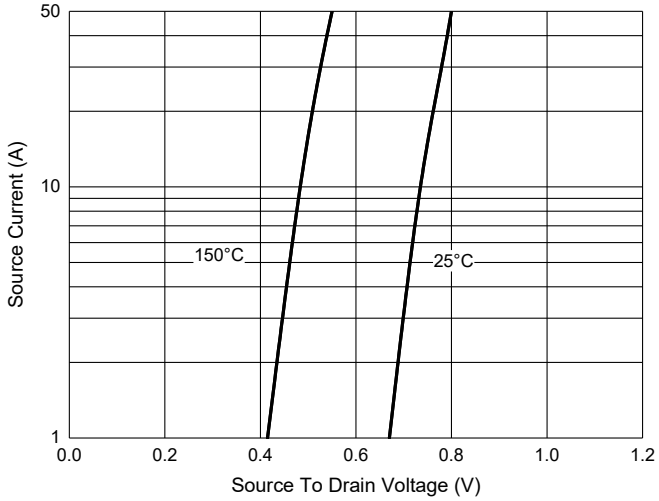
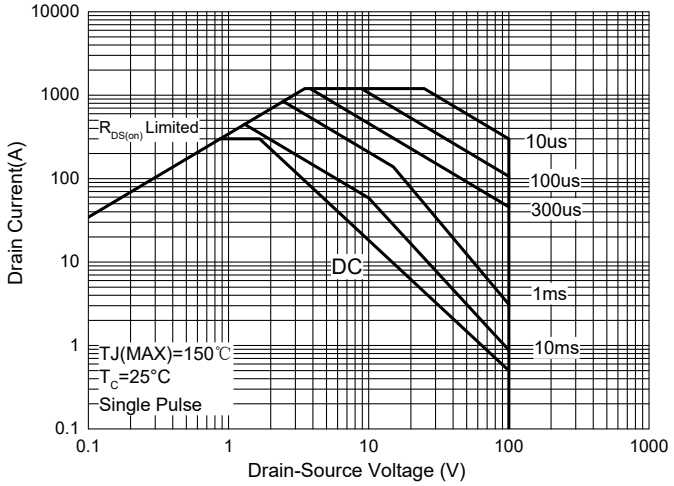


Fig. 8 - Safe Operation Area



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 2Kpcs/Reel

Note : Adding "-HF" Suffix For Halogen Free, eg. Part Number-TP-HF